

## **BUK6213-30A**

# N-channel TrenchMOS intermediate level FET Rev. 03 — 2 February 2011

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Intermediate level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for logic or standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	30	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	55	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	102	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \underline{\text{Figure 4}};$ $\text{see } \underline{\text{Figure 5}}$		-	10	13	mΩ
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 55 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ R_{GS} &= 50 \text{ \Omega; } V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 \text{ °C; } unclamped \end{split}$		-	-	267	mJ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 24 \text{ V}$		-	14	-	nC

<sup>[1]</sup> Continuous current is limited by bondwires.



## N-channel TrenchMOS intermediate level FET

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		G (EX)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6213-30A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<b>0</b> , ( )				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	45	A A A W °C
		$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ;	[2]	-	55	Α
		see <u>Figure 3</u>	[1]	-	- 64	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3		-	257	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	102	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	64	Α
			[2]	-	55	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	257	Α
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 55 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	267	mJ

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by bondwires.

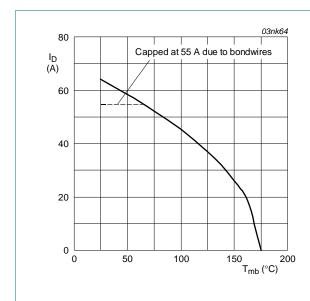
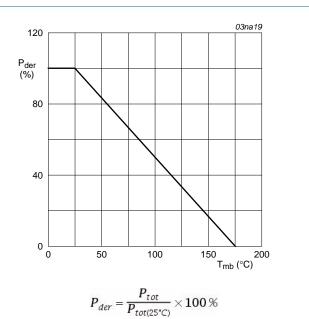


Fig 1. Continuous drain current as a function of mounting base temperature.



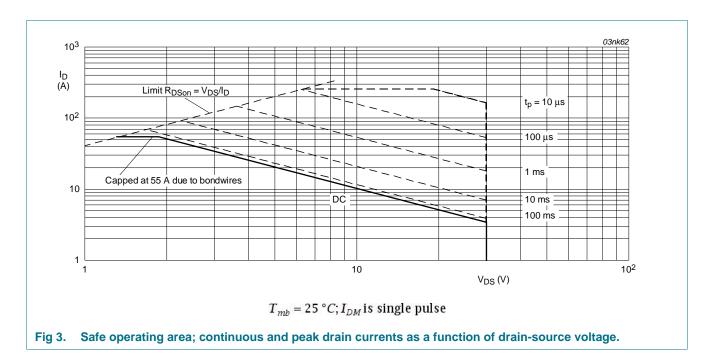
Normalized total power dissipation as a function of mounting base temperature

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### N-channel TrenchMOS intermediate level FET



## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	30	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.8	3	V
V <sub>GSth</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	3.5	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I <sub>GSS</sub> gat	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}$	-	15	20	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 ^{\circ}\text{C}$	-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 4</u> ; see <u>Figure 5</u>	-	10	13	mΩ
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### N-channel TrenchMOS intermediate level FET

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	500	μΑ
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 24 \text{ V}$ ; $V_{GS} = 10 \text{ V}$	-	44	-	nC
		$I_D = 25 \text{ A}$ ; $V_{DS} = 24 \text{ V}$ ; $V_{GS} = 5 \text{ V}$	-	26	-	nC
$Q_{GS}$	gate-source charge		-	7	-	nC
$Q_{GD}$	gate-drain charge		-	14	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1490	1986	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	505	606	pF
C <sub>rss</sub>	reverse transfer capacitance		-	325	445	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	12	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	95	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	75	-	ns
t <sub>f</sub>	fall time		-	105	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to center of die	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nΗ
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	49	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}$	-	27	-	nC

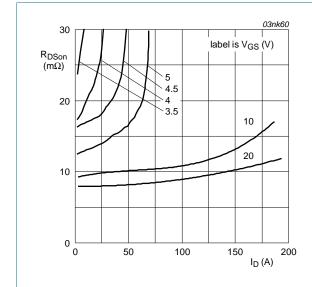


Fig 4. Drain-source on-state resistance as a function of drain current; typical values.

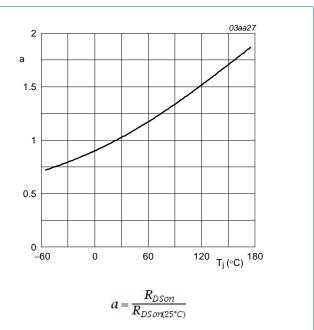


Fig 5. Normalized drain-source on-state resistance factor as a function of junction temperature

## 7. Package outline

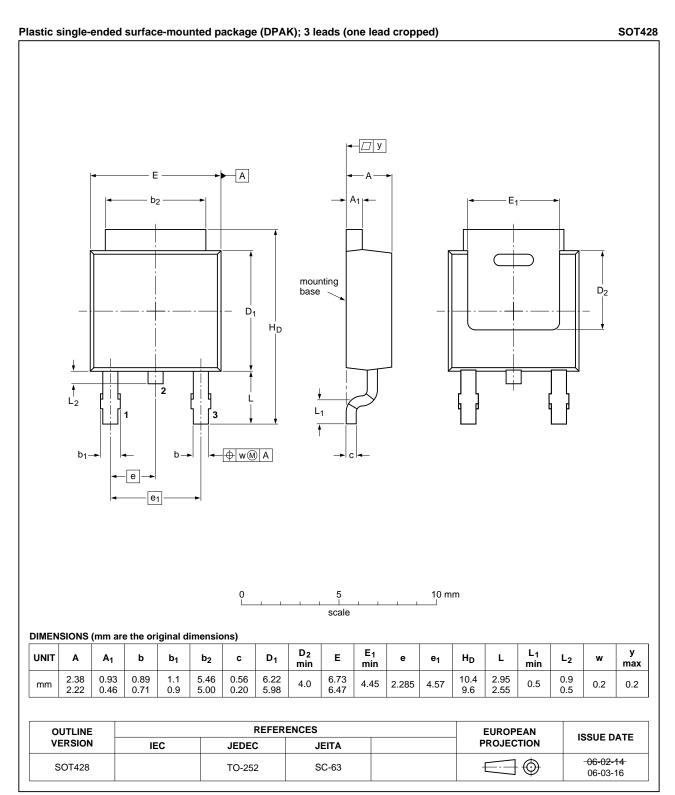


Fig 6. Package outline SOT428 (DPAK)

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## N-channel TrenchMOS intermediate level FET

## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6213-30A v.3	20110202	Product data sheet	-	BUK6213-30A v.2
Modifications:	of NXP Semicor	e been adapted to the new		
BUK6213-30A v.2 (9397 750 12028)	20030922	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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